

ABSOLUTE MAXIMUM RATINGS

Gate-Drain, Gate-Source Voltage -25 V
 Gate Current 10 mA
 Lead Temperature 300°C
 Storage Temperature -65 to 150°C

Operating Junction Temperature -55 to 150°C

Power Dissipation^a 350 mW

Notes

a. Derate 2.8 mW/°C above 25°C

SPECIFICATIONS FOR 2N SERIES (T _A = 25 °C UNLESS OTHERWISE NOTED)											
Parameter	Symbol	Test Conditions	Typ ^a	Limits						Unit	
				2N5484		2N5485		2N5486			
				Min	Max	Min	Max	Min	Max		
Static											
Gate-Source Breakdown Voltage	V _{(BR)GSS}	I _G = -1 μA , V _{DS} = 0 V	-35	-25		-25		-25		V	
Gate-Source Cutoff Voltage	V _{GS(off)}	V _{DS} = 15 V, I _D = 10 nA		-0.3	-3	-0.5	-4	-2	-6		
Saturation Drain Current ^b	I _{DSS}	V _{DS} = 15 V, V _{GS} = 0 V		1	5	4	10	8	20	mA	
Gate Reverse Current	I _{GSS}	V _{GS} = -20 V, V _{DS} = 0 V	-0.002		-1		-1		-1	nA	
		T _A = 100°C	-0.2		-200		-200		-200		
Gate Operating Current ^c	I _G	V _{DG} = 10 V, I _D = 1 mA	-20							pA	
Gate-Source Forward Voltage ^c	V _{GS(F)}	I _G = 10 mA , V _{DS} = 0 V	0.8							V	
Dynamic											
Common-Source Forward Transconductance ^{NO TAG}	g _{fs}	V _{DS} = 15 V, V _{GS} = 0 V f = 1 kHz		3	6	3.5	7	4	8	mS	
Common-Source Output Conductance ^{NO TAG}	g _{os}				50		60		75	μS	
Common-Source Input Capacitance	C _{iss}	V _{DS} = 15 V, V _{GS} = 0 V f = 1 MHz	2.2		5		5		5	pF	
Common-Source Reverse Transfer Capacitance	C _{rss}		0.7		1		1		1		
Common-Source Output Capacitance	C _{oss}		1		2		2		2		
Equivalent Input Noise Voltage ^c	e _n	V _{DS} = 15 V, V _{GS} = 0 V f = 100 Hz	10							nV/ √Hz	
High-Frequency											
Common-Source Transconductance ^d	Y _{fs(RE)}	V _{DS} = 15 V V _{GS} = 0 V	f = 100 MHz	5.5	2.5					mS	
			f = 400 MHz	5.5			3		3.5		
Common-Source Output Conductance ^d	Y _{os(RE)}		f = 100 MHz	45		75					μS
			f = 400 MHz	65				100		100	
Common-Source Input Conductance ^d	Y _{is(RE)}		f = 100 MHz	0.05		0.1					mS
			f = 400 MHz	0.8				1		1	
Common-Source Power Gain ^d	G _{ps}	V _{DS} = 15 V, I _D = 1 mA f = 100 MHz		20	16	25				dB	
		V _{DS} = 15 V I _D = 4 mA	f = 100 MHz	21		18	30	18	30		
			f = 400 MHz	13		10	20	10	20		
Noise Figure ^d	NF	V _{DS} = 15 V, V _{GS} = 0 V R _G = 1 MΩ, f = 1 kHz		0.3		2.5		2.5			2.5
		V _{DS} = 15 V, I _D = 1 mA R _G = 1 kΩ, f = 100 MHz		2		3					
		V _{DS} = 15 V I _D = 4 mA R _G = 1 kΩ	f = 100 MHz	1			2		2		
			f = 400 MHz	2.5			4		4		



SPECIFICATIONS FOR SST SERIES (T _A = 25°C UNLESS OTHERWISE NOTED)										
Parameter	Symbol	Test Conditions	Typ ^b	Limits						Unit
				SST5484		SST5485		SST5486		
				Min	Max	Min	Max	Min	Max	
Static										
Gate-Source Breakdown Voltage	V _{(BR)GSS}	I _G = -1 μA , V _{DS} = 0 V	-35	-25		-25		-25		V
Gate-Source Cutoff Voltage	V _{GS(off)}	V _{DS} = 15 V, I _D = 10 nA		-0.3	-3	-0.5	-4	-2	-6	
Saturation Drain Current ^b	I _{DSS}	V _{DS} = 15 V, V _{GS} = 0 V		1	5	4	10	8	20	mA
Gate Reverse Current	I _{GSS}	V _{GS} = -20 V, V _{DS} = 0 V	-0.002		-1		-1		-1	nA
		T _A = 100°C	-0.2		-200		-200		-200	
Gate Operating Current ^c	I _G	V _{DG} = 10 V, I _D = 1 mA	-20							pA
Gate-Source Forward Voltage ^c	V _{GS(F)}	I _G = 10 mA , V _{DS} = 0 V	0.8							V
Dynamic										
Common-Source Forward Transconductance ^{NO TAG}	g _{fs}	V _{DS} = 15 V, V _{GS} = 0 V f = 1 kHz		3	6	3.5	7	4	8	mS
Common-Source Output Conductance ^{NO TAG}	g _{os}				50		60		75	μS
Common-Source Input Capacitance	C _{iss}	V _{DS} = 15 V, V _{GS} = 0 V f = 1 MHz	2.2							pF
Common-Source Reverse Transfer Capacitance	C _{rss}		0.7							
Common-Source Output Capacitance	C _{oss}		1							
Equivalent Input Noise Voltage ^c	e _n	V _{DS} = 15 V, V _{GS} = 0 V f = 100 Hz	10							nV/ √Hz
High-Frequency										
Common-Source Transconductance	Y _{fs}	V _{DS} = 15 V V _{GS} = 0 V	f = 100 MHz	5.5						mS
			f = 400 MHz	5.5						
Common-Source Output Conductance	Y _{os}		f = 100 MHz	45						μS
			f = 400 MHz	65						
Common-Source Input Conductance	Y _{is}		f = 100 MHz	0.05						mS
			f = 400 MHz	0.8						
Common-Source Power Gain	G _{ps}	V _{DS} = 15 V, I _D = 1 mA f = 100 MHz		20						dB
		V _{DS} = 15 V I _D = 4 mA	f = 100 MHz	21						
			f = 400 MHz	13						
Noise Figure	NF	V _{DS} = 15 V, V _{GS} = 0 V R _G = 1 MΩ, f = 1 kHz		0.3						
		V _{DS} = 15 V, I _D = 1 mA R _G = 1 kΩ, f = 100 MHz		2						
		V _{DS} = 15 V I _D = 4 mA R _G = 1 kΩ	f = 100 MHz	1						
			f = 400 MHz	2.5						

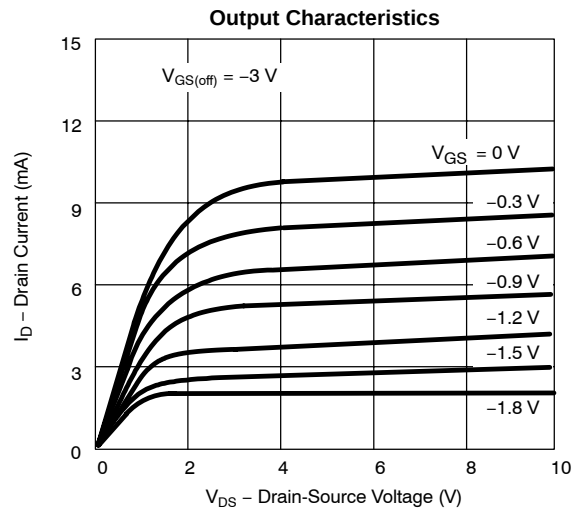
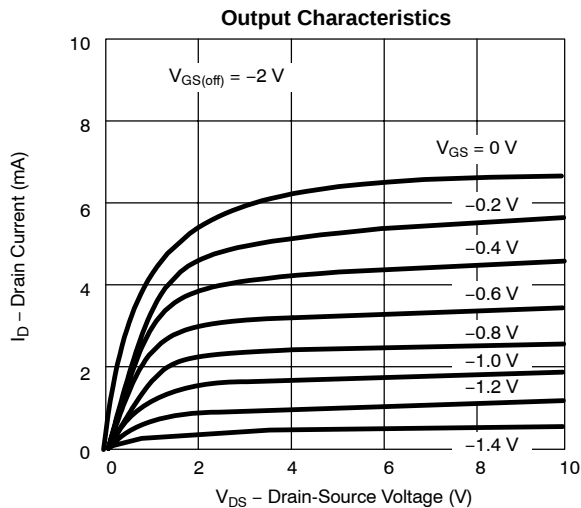
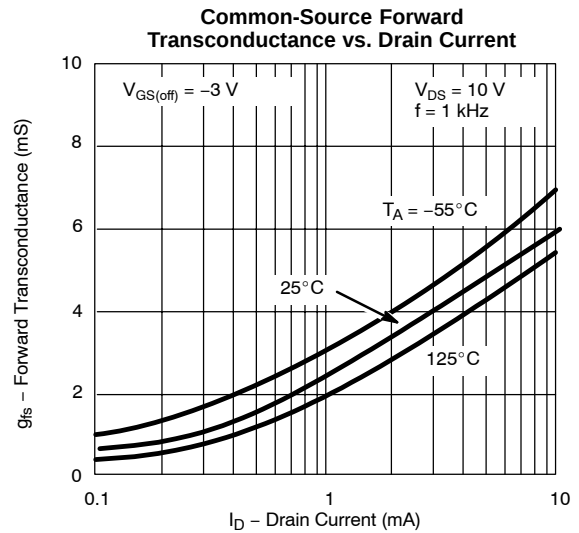
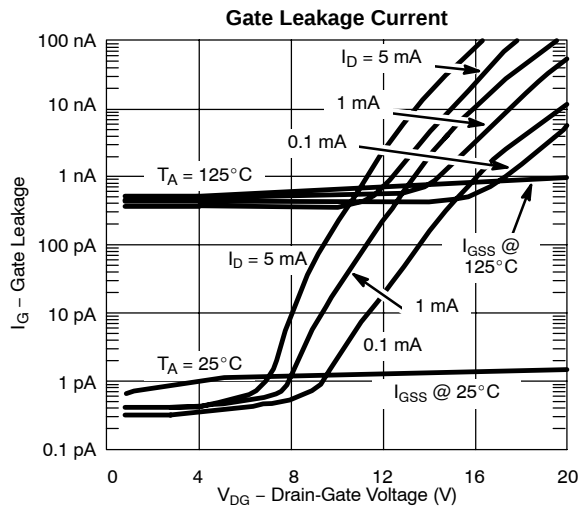
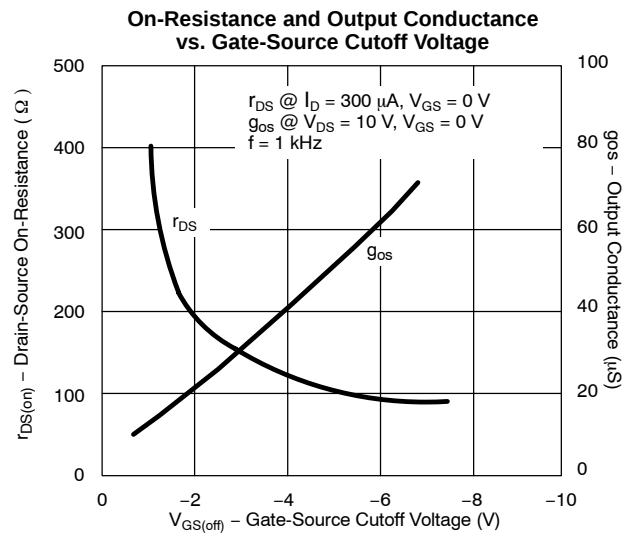
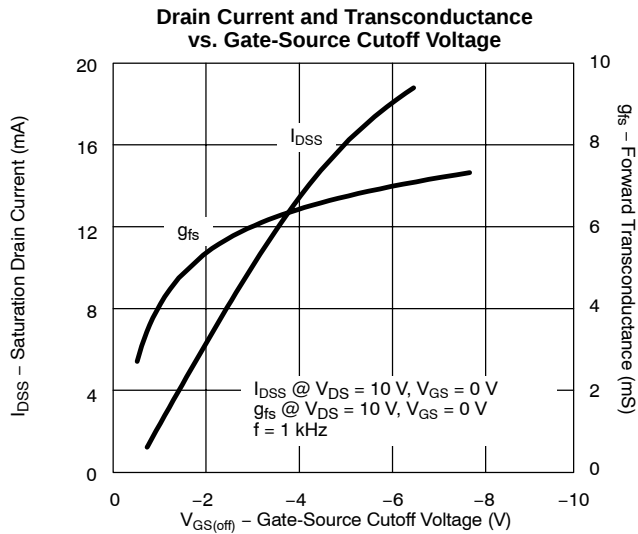
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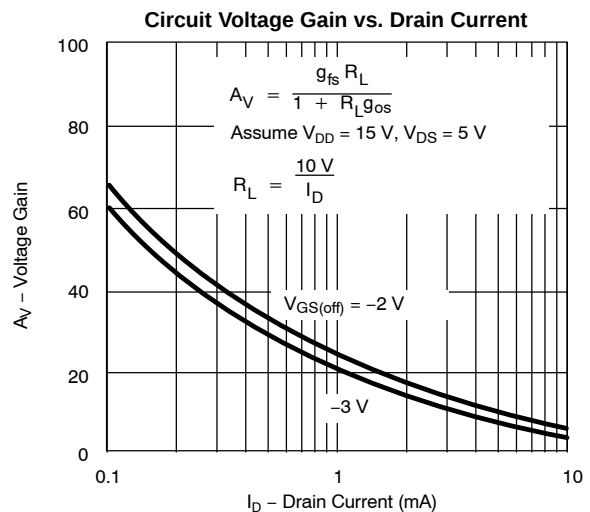
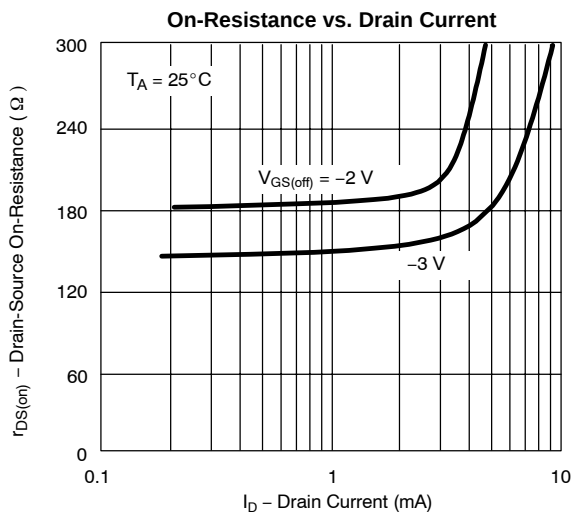
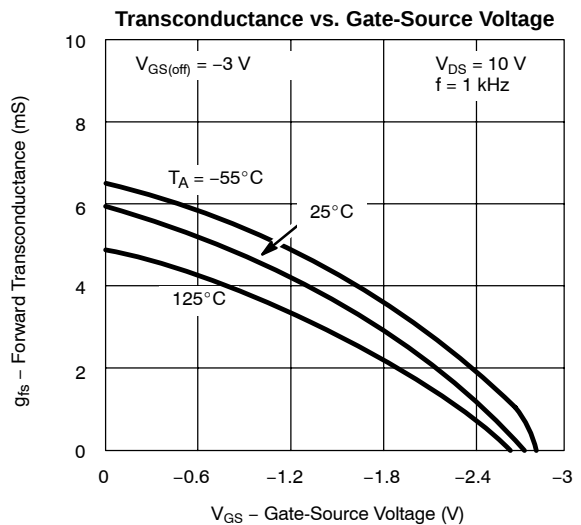
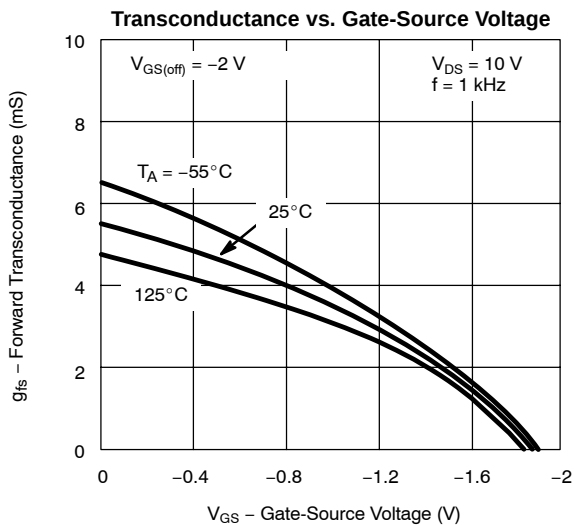
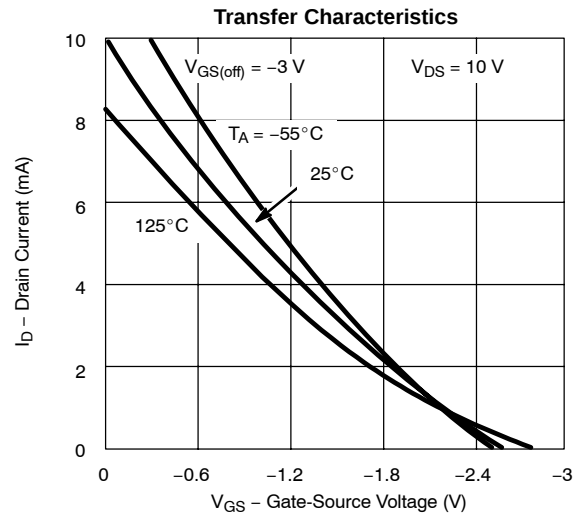
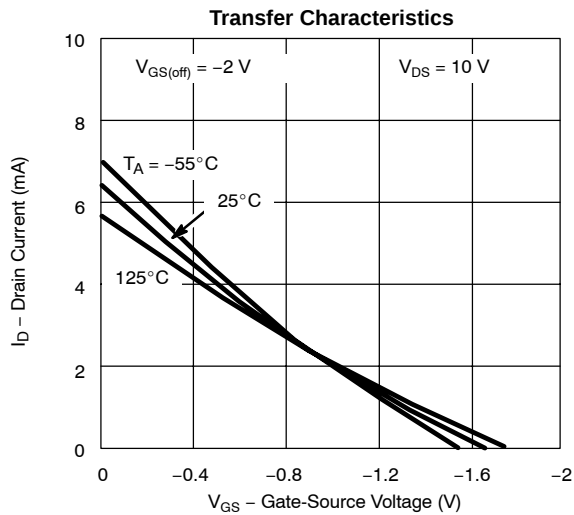
- a. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
b. Pulse test: PW ≤ 300 μs duty cycle ≤ 3%.
c. This parameter not registered with JEDEC.
d. Not a production test.

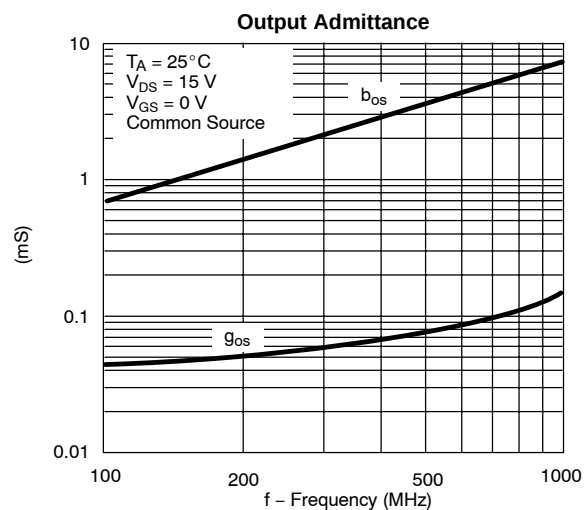
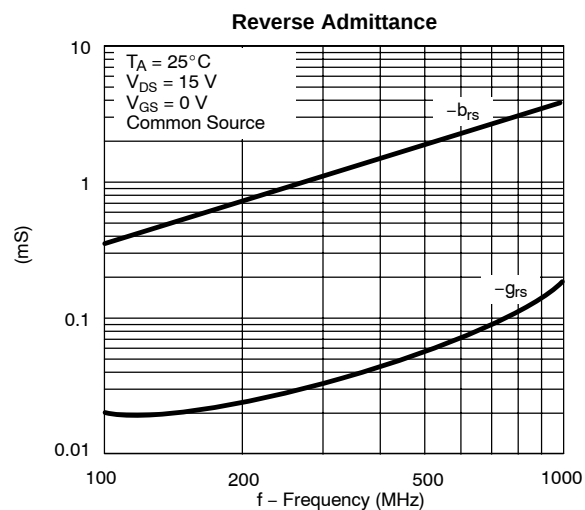
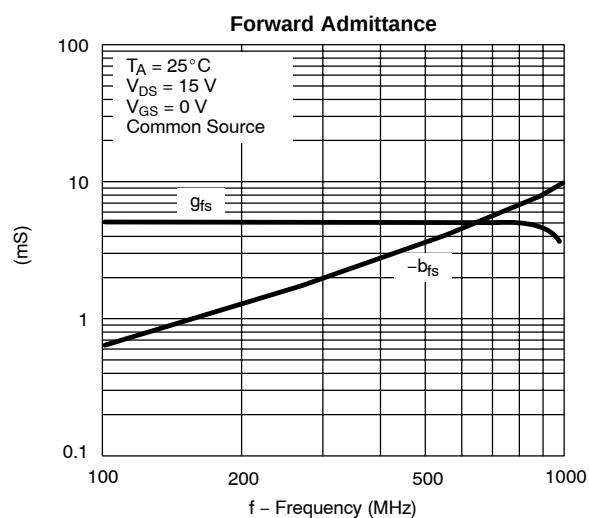
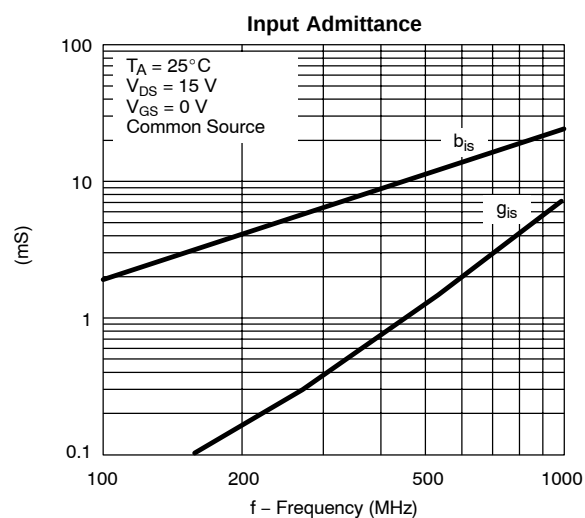
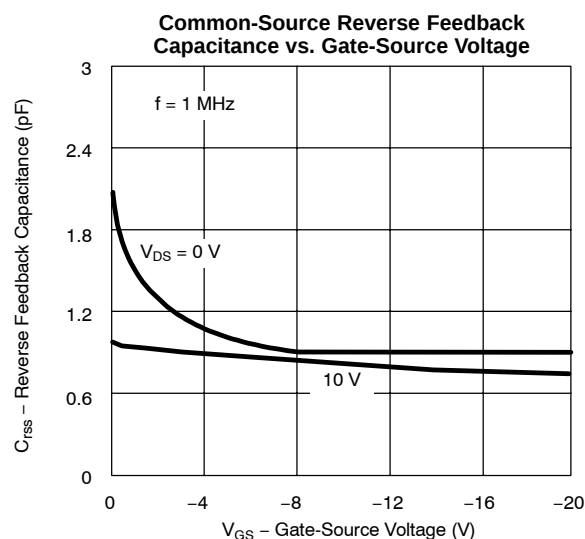
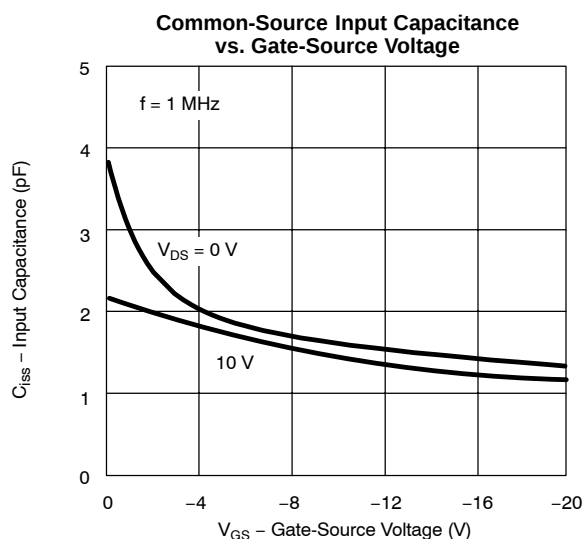
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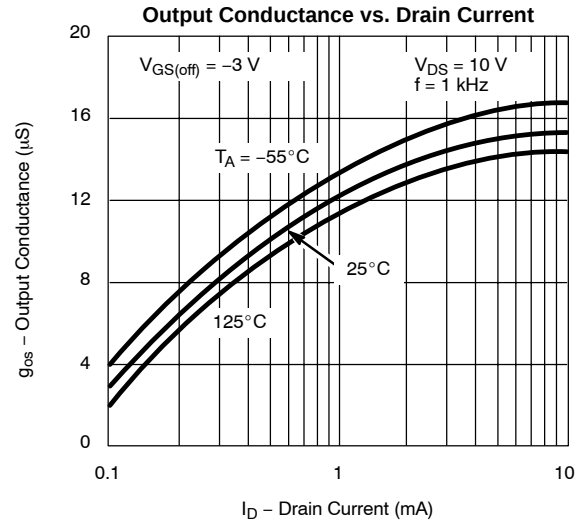
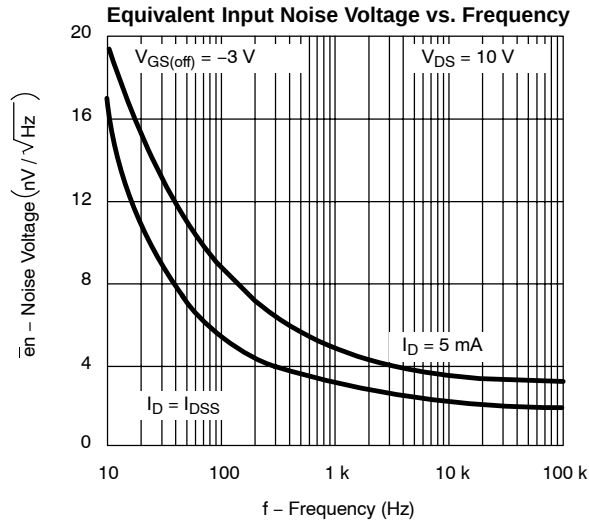
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)



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